

L15 ANSWER 12 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN

AN 1995:995408 HCAPLUS

DN 124:133984

TI Tantalum compounds

IN Leedham, Timothy John; Drake, Simon Robert

PA UK

SO PCT Int. Appl., 37 pp.

CODEN: PIXXD2

DT Patent

LA English

IC ICM C07F009-00

ICS C23C016-40

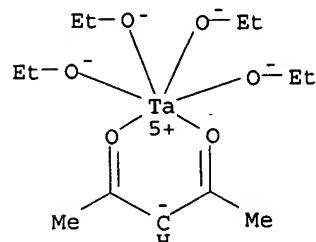
CC 78-7 (Inorganic Chemicals and Reactions)

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 9526355	A1	19951005	WO 1995-GB644	19950323
	W: AM, AT, AU, BB, BG, BR, BY, CA, CH, CN, CZ, DE, DK, EE, ES, FI, GB, GE, HU, IS, JP, KE, KG, KP, KR, KZ, LK, LR, LT, LU, LV, MD, MG, MN, MW, MX, NL, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, TJ, TT				
	RW: KE, MW, SD, SZ, UG, AT, BE, CH, DE, DK, ES, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, BF, BJ, CF, CG, CI, CM, GA, GN, ML, MR, NE, SN, TD, TG				
	AU 9519553	A1	19951017	AU 1995-19553	19950323
PRAI	GB 1994-6060			19940326	
	GB 1994-23750			19941124	
	WO 1995-GB644			19950323	
AB	Ta(OR) <sub>5-n</sub> X <sub>n</sub> (n = 1, 2 or 3; each R is independently selected from a straight or branched chain alkyl group having between 1 and 4 C atoms, or SiMe <sub>3</sub> ; and X is a bidentate ligand) were prepd. These compds. may be used as precursors for metal org. CVD (MOCVD) of oxide layers in applications such as integrated circuit dielectrics, microwaves, optical coatings and catalysts.				
	RL: IMF (Industrial manufacture); RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent) (prepn. and use in MOCVD for prepn. of tantalum oxide)				

RN 20219-33-4 HCAPLUS

CN Tantalum, tetraethoxy(2,4-pentanedionato-.kappa.O,.kappa.O')-, (OC-6-22)- (9CI) (CA INDEX NAME)



RN 172901-18-7 HCAPLUS

CN Tantalum, tetraethoxy[2-(methoxy-.kappa.O)ethanolato-.kappa.O]-, (OC-6-33)- (9CI) (CA INDEX NAME)

→ See chem  
structure

on  
next sheet.

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